

Comparison of Doped and High-Resistivity Silicon Interposers for Heterogeneous Integration of Millimeter-Wave Circuits

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We compare the millimeter-wave loss of coplanar interconnects fabricated on Si interposers with different resistivities. Coplanar interconnects 2146- μ m long are laid out on two types of Si substrates: HR Si (resistivity $> 1 \text{ k}\Omega\cdot\text{cm}$, thickness = 155 μ m) and doped Si (resistivity $< 10 \text{ }\Omega\cdot\text{cm}$, thickness = 205 μ m). The widths of the center electrode of the coplanar interconnects and its gap to the ground electrode are 30 μ m and 16 μ m, respectively, resulting in a characteristic impedance $\approx 50 \Omega$. The ground electrodes are grounded by a high density of through-silicon vias (TSVs) to suppress higher-order modes. To mitigate the residual stress from thermal expansion mismatch, TSVs are metallized with Al having an annular structure (Fig. 1) [1]. Small-signal measurements from 1 GHz to 40 GHz indicate the advantages of high-resistivity (HR) Si interposers for heterogeneous integration of millimeter-wave circuits.

Front-side wafer fabrication comprises mainly sputtering of 20-nm Ti and 1.5- μ m Al and patterning by liftoff. The most critical steps of backside fabrication involve etching and metallizing 50- μ m-diameter TSVs. Using the Bosch process [2] with a 200-nm Al_2O_3 hard mask, the substrates are deep etched from the backside at an etch rate of 27 nm/s. TSV metallization is then carried out by depositing 50- nm Pt using atomic layer deposition [3], followed by 70-nm Ti and 2- μ m Al using sputtering (Fig. 2) [4]. DC measurements confirm a TSV series resistance on the order of 1 Ω . Small-signal millimeter-wave on-wafer measurements (Fig. 3) show the coplanar interconnects fabricated on HR Si have an insertion loss of 0.7 dB/mm at 40 GHz (Fig. 4), an order of magnitude better than the same coplanar interconnects fabricated on doped Si. The return loss of the coplanar interconnects fabricated on HR Si is always greater than 20 dB between 1 and 40 GHz.

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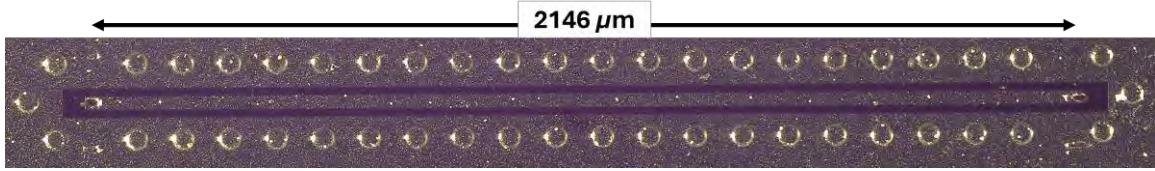


Fig. 1. Micrograph showing a 2146- μm -long grounded coplanar interconnect within two parallel rows of TSVs to prevent higher-order modes from propagating.

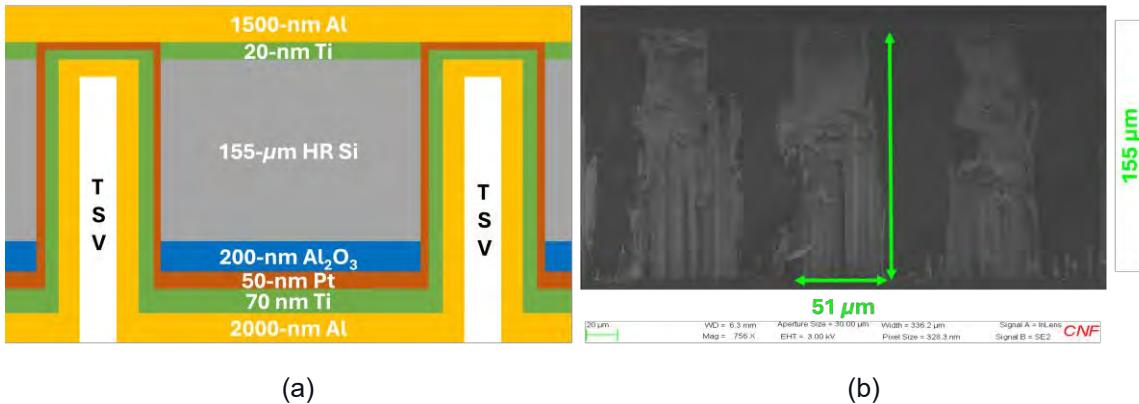


Fig. 2. Cross-section (a) schematics and (b) SEM image of a metallized through-Si via (TSV).

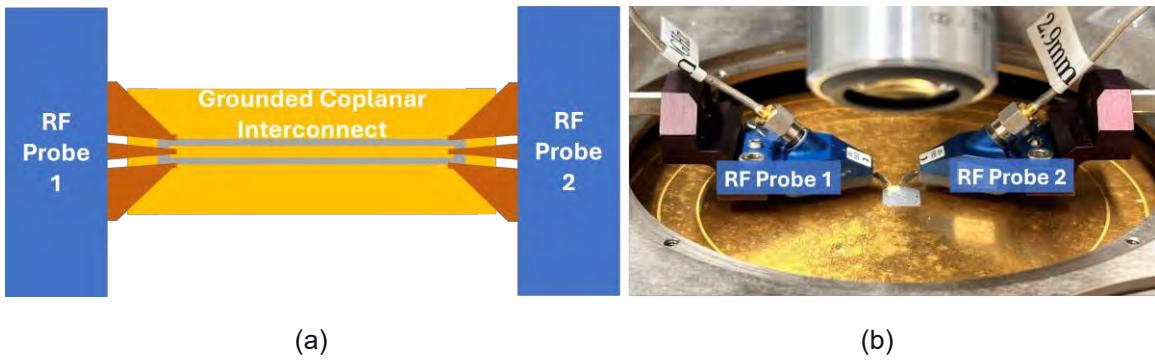


Fig. 4. (a) Schematic and (b) photograph of coplanar interconnect under millimeter-wave test.

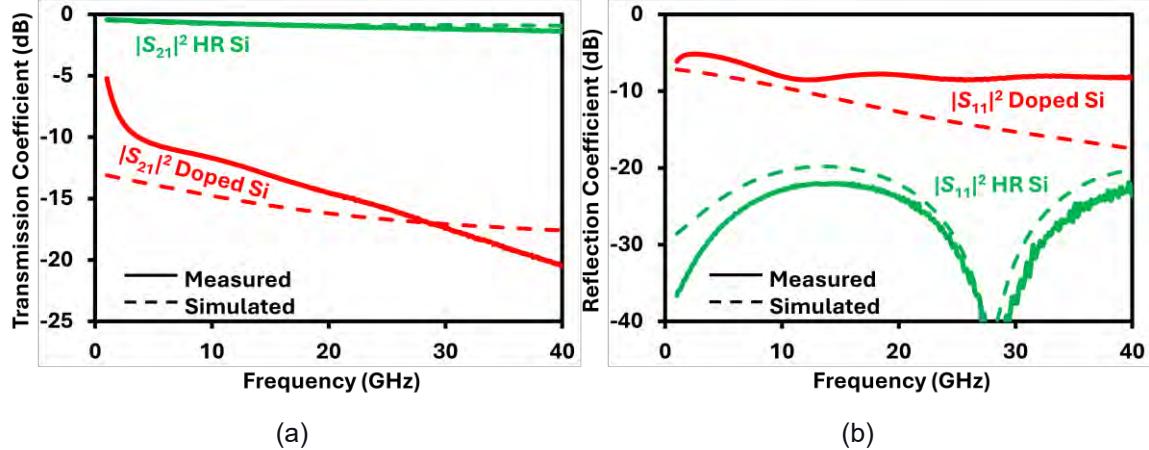


Fig. 4. Measured vs. simulated (a) transmission and (b) reflection coefficients of a 2146- μm -long grounded coplanar interconnects fabricated on doped and high resistivity (HR) Si interposers.